New Jersey Semi-Conductor Products, Inc.

20 STERN AVE.
SPRINGFIELD, NEW JERSEY 07081
U.S.A.

TELEPHONE: (973) 376-2922
(212) 227-6005
FAX: (973) 376-8960

2N656
2N657

NPN SILICON TRANSISTOR

JEDEC TO-39 CASE

MAXIMUM RATINGS ($T_A = 25^oC$)

	SYMBOL	2N656	2N657	UNITS
Collector-Base Voltage	V_{CBO}	60	100	V
Collector-Emitter Voltage	V_{CEO}	60	100	V
Emitter-Base Voltage	V_{EBO}	8.0	8.0	V
Collector Current	I_C	1.0	0.5	A
Power Dissipation	P_D	1.0		W
Power Dissipation ($T_C = 25^oC$)	P_D	4.0		W
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +200		^oC
Thermal Resistance	θ_{JA}	175		$^oC/W$
Thermal Resistance	θ_{JC}	43.75		$^oC/W$

ELECTRICAL CHARACTERISTICS ($T_A = 25^oC$ unless otherwise noted)

		2N656		2N657		
SYMBOL	TEST CONDITIONS	MIN	MAX	MIN	MAX	UNITS
I_{CBO}	$V_{CB} = 30V$		10		10	μA
BV_{CBO}	$I_C = 100\mu A$	60		100		V
BV_{CEO}	$I_C = 250\mu A$	60		100		V
BV_{EBO}	$I_E = 250\mu A$	8.0		8.0		V
$V_{CE(SAT)}$	$I_C = 200mA, I_B = 40mA$		4.0		4.0	V
h_{FE}	$V_{CE} = 10V, I_C = 200mA$	30	90	30	90	
h_{ie}	$V_{CE} = 10V, I_B = 8.0mA$		0.5		0.5	kΩ